



IRF6644TRPBF Information



For Reference Only

Part Number IRF6644TRPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 10.3A DIRECTFET

Package DirectFET? Isometric MN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF6644TRPBF Specifications

Manufacturer Part Number IRF6644TRPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package DirectFET? Isometric MN Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10.3A (Ta), 60A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.8V @ 150µA Gate Charge (Qg) (Max) @ Vgs 47nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2210pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.8W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 13 mOhm @ 10.3A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package DIRECTFET? MN Package / Case DirectFET? Isometric MN		
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Mounting Type Surface Mount Supplier Device Package DIRECTFET? MN Package / Case DirectFET? Isometric MN	Rds On (Max) @ Id, Vgs	13 mOhm @ 10.3A, 10V
Supplier Device Package DIRECTFET? MN Package / Case DirectFET? Isometric MN	Operating Temperature	-40°C ~ 150°C (TJ)
Package / Case DirectFET? Isometric MN	Mounting Type	Surface Mount
	Supplier Device Package	DIRECTFET? MN
Report errors?	Package / Case	DirectFET? Isometric MN
		Report errors?

IRF6644TRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF6644TRPBF Payment Methods



















IRF6644TRPBF Shipping Methods













If you have any question about IRF6644TRPBF, please do not hesitate to contact us!

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